# **Dual 2-Input OR Gate**

The NL27WZ32 is a high performance dual 2-input OR Gate operating from a 1.65 V to 5.5 V supply.

- Extremely High Speed:  $t_{PD}$  2.5 ns (typical) at  $V_{CC} = 5 \text{ V}$
- Designed for 1.65 V to 5.5 V V<sub>CC</sub> Operation
- Over Voltage Tolerant Inputs
- $\bullet\,$  LVTTL Compatible Interface Capability With 5 V TTL Logic with  $V_{CC}$  = 3 V
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Replacement for NC7WZ32
- Chip Complexity: FET = 120

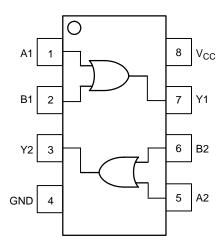


Figure 1. Pinout

#### **PIN ASSIGNMENT**

Pin	Function
1	A1
2	B1
3	Y2
4	GND
5	A2
6	B2
7	Y1
8	V <sub>CC</sub>



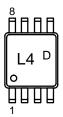
# ON Semiconductor®

### http://onsemi.com

MARKING DIAGRAM



US8 US SUFFIX CASE 493



D = Date Code

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

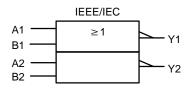


Figure 2. Logic Symbol

#### **FUNCTION TABLE**

Inp	Output Y = A + B	
Α	В	Y
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

#### **MAXIMUM RATINGS**

Symbol	F	arameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
VI	DC Input Voltage		-0.5  to  +7.0	V
Vo	DC Output Voltage		-0.5  to  +7.0	V
I <sub>IK</sub>	DC Input Diode Current	V <sub>I</sub> < GND	-50	mA
I <sub>OK</sub>	DC Output Diode Current	V <sub>O</sub> < GND	-50	mA
Io	DC Output Sink Current		±50	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin		±100	mA
I <sub>GND</sub>	DC Ground Current per Ground Pin		±100	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
T <sub>L</sub>	Lead Temperature, 1 mm from Case	for 10 Seconds	260	°C
TJ	Junction Temperature under Bias		+150	°C
$\theta_{JA}$	Thermal Resistance	(Note 1)	250	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 85°C		250	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V
I <sub>Latch-Up</sub>	Latch-Up Performance Above V <sub>CC</sub>	and Below GND at 85°C (Note 5)	±500	mA

Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If stress limits are exceeded device functional operation is not implied, damage may occur and reliability may be affected. Functional operation should be restricted to the Recommended Operating Conditions.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	Supply Voltage	Operating Data Retention Only			
VI	Input Voltage	(Note 6)	0	5.5	V
V <sub>O</sub>	Output Voltage	(HIGH or LOW State)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Free–Air Temperature		-40	+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate	$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V} \\ V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V} \\ V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V} \\ V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0 0	20 20 10 5	ns/V

6. Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

# DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>	TA	$T_A = +25^{\circ}C$		$T_A = -40^{\circ}C$	to +85°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	HIGH Level Input Voltage		1.65 to 1.95	0.75 V <sub>CC</sub> 0.7 V <sub>CC</sub>			0.75 V <sub>CC</sub> 0.7 V <sub>CC</sub>		V
V <sub>IL</sub>	LOW Level Input Voltage		1.65 to 1.95 2.3 to 5.5			0.3 V <sub>CC</sub>		0.3 V <sub>CC</sub>	V
V <sub>OH</sub>	HIGH Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub>	I <sub>OH</sub> = -100 μA	1.65 2.3 3.0 4.5	1.55 2.2 2.9 4.4	1.65 2.3 3.0 4.5		1.55 2.2 2.9 4.4		V
		$I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$ $I_{OH} = -16 \text{ mA}$ $I_{OH} = -24 \text{ mA}$ $I_{OH} = -32 \text{ mA}$	1.65 2.3 3.0 3.0 4.5	1.29 1.9 2.4 2.3 3.8	1.52 2.15 2.8 2.68 4.2		1.20 1.9 2.4 2.3 3.8		
V <sub>OL</sub>	Low-Level Output Voltage V <sub>IN</sub> = V <sub>IL</sub>	Ι <sub>ΟL</sub> = 100 μΑ	1.65 2.3 3.0 4.5		0 0 0 0	0.1 0.1 0.1 0.1			V
		I <sub>OH</sub> = 4 mA I <sub>OH</sub> = 8 mA I <sub>OH</sub> = 16 mA I <sub>OH</sub> = 24 mA I <sub>OH</sub> = 32 mA	1.65 2.3 3.0 3.0 4.5		0.08 0.1 0.15 0.22 0.22	0.24 0.3 0.4 0.55 0.55			
I <sub>IN</sub>	Input Leakage Current	$V_{IN} = V_{CC}$ or GND	0 to 5.5			± 0.1		±1.0	μΑ
I <sub>OFF</sub>	Power OFF Leakage Current	$V_{IN}$ or $V_{OUT} = 5.5 \text{ V}$	0.0			1.0		10	
I <sub>CC</sub>	Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		10	μΑ

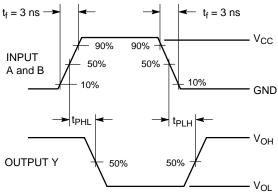
# AC ELECTRICAL CHARACTERISTICS $t_R = t_F = 3.0 \text{ ns}$

			V <sub>CC</sub>	-	T <sub>A</sub> = 25°C		$-40^{\circ}\text{C}\leq\text{T}_{\text{A}}\leq85^{\circ}\text{C}$		
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub>	Propagation Delay (Figure 3 and 4)	$R_L = 1 M\Omega$ , $C_L = 15 pF$	1.8 ± 0.15 2.5 ± 0.2	2.0 1.0	8.0 3.5	9.5 5.8	2.0 1.0	10.5 6.2	ns
t <sub>PHL</sub>		$R_L = 1 \text{ M}\Omega$ , $C_L = 15 \text{ pF}$	$3.3 \pm 0.3$	0.8	2.6	3.9	0.8	4.3	
		$R_L = 500 \ \Omega, \ C_L = 50 \ pF$		1.2	3.2	4.8	1.2	5.2	
		$R_L = 1 \text{ M}\Omega, C_L = 15 \text{ pF}$	$5.0 \pm 0.5$	0.5	1.9	3.1	0.5	3.3	
		$R_L = 500 \ \Omega, C_L = 50 \ pF$		0.8	2.5	3.7	0.8	4.0	

# **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Condition	Typical	Unit
C <sub>IN</sub>	Input Capacitance	$V_{CC}$ = 5.5 V, $V_I$ = 0 V or $V_{CC}$	2.5	pF
C <sub>PD</sub>	Power Dissipation Capacitance	10 MHz, $V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	9	pF
	(Note 7)	10 MHz, $V_{CC}$ = 5.5 V, $V_{I}$ = 0 V or $V_{CC}$	11	

<sup>7.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \cdot C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .



V<sub>OL</sub>

Let V<sub>OH</sub>

V<sub>OL</sub>

A 1-MHz square input wave is recommended for propagation delay tests.

**INPUT** 

Figure 3. Switching Waveform

Figure 4. Test Circuit

OUTPUT

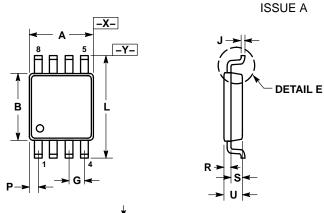
# **DEVICE ORDERING INFORMATION**

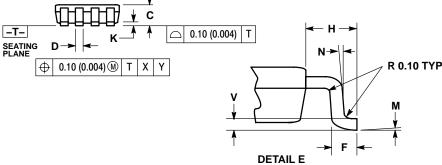
	Device Nomenclature							
Device Order Number	Logic Circuit Indicator	No. of Gates per Package	Temp Range Identifier	Technol- ogy	Device Function	Package Suffix	Package Type	Tape and Reel Size <sup>†</sup>
NL27WZ32US	NL	2	7	WZ	32	US	US8	178 mm, 3000 Unit

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **PACKAGE DIMENSIONS**

# US8 **US SUFFIX** CASE 493-01





#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER
   ANSI Y14.5M, 1982.
   2. CONTROLLING DIMENSION: MILLIMETERS.
   3. DIMENSION "A" DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURR. MOLD FLASH. PROTRUSION AND GATE
- MOLD FLASH. PROTRUSION AND GATE BURR SHALL NOT EXCEED 0.140 MM (0.0055") PER SIDE.

  4. DIMENSION "B" DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSION. INTER-LEAD FLASH AND PROTRUSION SHALL NOT E3XCEED 0.140 (0.0055") PER SIDE.

  5. LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 0.0076-0.0203 MM. (300-800").

  6. ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 (0.0002").
- SPECIFIED ±0.0508 (0.0002 ").

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	1.90	2.10	0.075	0.083	
В	2.20	2.40	0.087	0.094	
С	0.60	0.90	0.024	0.035	
D	0.17	0.25	0.007	0.010	
F	0.20	0.35	0.008	0.014	
G	0.50	BSC	0.020	BSC	
Н	0.40	REF	0.016 REF		
J	0.10	0.18	0.004	0.007	
K	0.00	0.10	0.000	0.004	
L	3.00	3.20	0.118	0.126	
М	0 °	6°	0 °	6°	
N	5 °	10 °	5 °	10 °	
Р	0.23	0.34	0.010	0.013	
R	0.23	0.33	0.009	0.013	
S	0.37	0.47	0.015	0.019	
U	0.60	0.80	0.024	0.031	
V	0.12	BSC	0.005 BSC		

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